











**TPS735** SBVS087M - JUNE 2008 - REVISED JUNE 2018

# TPS735 500-mA, Low Quiescent Current, Low Noise, High PSRR, **Low-Dropout Linear Regulator**

# **Features**

- Input Voltage: 2.7 V to 6.5 V
- 500-mA Low-Dropout Regulator With EN
- Low I<sub>O</sub>: 45 μA
- Multiple Output Voltage Versions Available:
  - Fixed Outputs of 1.2 V to 4.3 V
  - Adjustable Outputs from 1.25 V to 6 V
- High PSRR: 68 dB at 1 kHz
- Low Noise: 13.2 μV<sub>RMS</sub>
- Fast Start-Up Time: 45 μs
- Stable With a Ceramic, 2.2-µF, Low-ESR Output Capacitor
- **Excellent Load and Line Transient Response**
- 2% Overall Accuracy (Load, Line, and Temperature,  $V_{OUT} > 2.2 \text{ V}$
- Very Low Dropout: 280 mV at 500 mA
- 2-mm × 2-mm WSON-6 and 3-mm × 3-mm SON-8 Packages

# **Applications**

- Post DC-DC Converter Ripple Filtering
- **IP Network Cameras**
- Macro Base Stations
- **Thermostats**

# 3 Description

The TPS735 low-dropout (LDO), low-power linear regulator offers excellent AC performance with very low ground current. High power-supply rejection ratio (PSRR), low noise, fast start-up, and excellent line and load transient responses are provided while consuming a very low 45-µA (typical) ground current.

The TPS735 device is stable with ceramic capacitors and uses an advanced BiCMOS fabrication process to yield a typical dropout voltage of 280 mV at 500mA output. The TPS735 device uses a precision voltage reference and feedback loop to achieve overall accuracy of 2% (V<sub>OUT</sub> > 2.2 V) over all load, line, process, and temperature variations. This device is fully specified from  $T_J = -40^{\circ}\text{C}$  to +125°C and is offered in a low-profile, 3 mm × 3 mm SON-8 package and a 2 mm × 2 mm WSON-6 package.

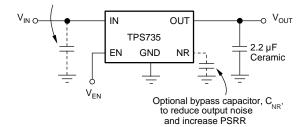
#### Device Information<sup>(1)</sup>

PART NUMBER	PACKAGE	BODY SIZE (NOM)	
TD0705	WSON (6)	2.00 mm × 2.00 mm	
TPS735	SON (8)	3.00 mm × 3.00 mm	

(1) For all available packages, see the orderable addendum at the end of the data sheet.

# **Typical Application**

Optional input capacitor,  $C_{IN}$ , to improve source impedance, noise, and PSRR





# **Table of Contents**

1	Features 1	8	Application and Implementation	13
2	Applications 1		8.1 Application Information	13
3	Description 1		8.2 Typical Applications	13
4	Revision History2	9	Power Supply Recommendations	16
5	Pin Configuration and Functions 4	10	Layout	16
6	Specifications5		10.1 Layout Guidelines	16
•	6.1 Absolute Maximum Ratings 5		10.2 Layout Example	16
	6.2 ESD Ratings		10.3 Power Dissipation	17
	6.3 Recommended Operating Conditions		10.4 Estimating Junction Temperature	18
	6.4 Thermal Information		10.5 Package Mounting	19
	6.5 Electrical Characteristics	11	Device and Documentation Support	20
	6.6 Typical Characteristics8		11.1 Device Support	20
7	Detailed Description 10		11.2 Documentation Support	<mark>20</mark>
•	7.1 Overview		11.3 Trademarks	20
	7.2 Functional Block Diagrams		11.4 Electrostatic Discharge Caution	20
	7.3 Feature Description		11.5 Glossary	20
	7.4 Device Functional Modes		Mechanical, Packaging, and Orderable Information	20

# 4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

CI	nanges from Revision L (January 2015) to Revision M	Page
•	Updated data sheet text to latest data sheet and translation standards	1
•	Changed "Ultra-Low Noise" to "Low Noise" in document title	1
•	Changed Low I <sub>Q</sub> from 46 μA to 45 μA in <i>Features</i> , <i>Description</i> , and <i>Application Information</i> sections	1
•	Changed "Standard" to "Ceramic" in Features list	
•	Changed 6-pin package from "SON" to "WSON" in Features list	1
•	Deleted printers, WiFi®, WiMax Modules, cellular phones, smart phones and microprocessor power from Applications section	1
•	Added post DC/DC ripple filtering, IP network cameras, macro base stations, and thermostats to <i>Applications</i> sections.	
•	Changed T <sub>A</sub> to T <sub>J</sub> in <i>Description</i> section	
•	Changed 6-pin package from "SON" to "WSON" in <i>Description</i> section	
•	Changed package in <i>Device Information</i> table from VSON (6) to WSON (6)	
•	Changed 6-pin DRB package designator from "VSON" to "SON" in Pin Configurations and Functions section	
•	Changed 6-pin DRV package designator from "VSON" to "WSON" in Pin Configurations and Functions section	4
•	Added "feedback resistor" parameter to Recommended Operating Conditions table	5
•	Changed DRV package designator from "VSON" to "WSON" in Thermal Information table	6
•	Changed DRB package designator from "VSON" to "SON" in Thermal Information table	6
•	Changed TPS735 Ground Pin Current (Disable) vs Temperature in Typical Characteristics section	8
•	Changed TPS735 Dropout Voltage vs Output Current in Typical Characteristics section	8
•	Updated Equation 1	14
•	Changed x-axis scale from "10 ms/div" to "10 µs/div" in Figure 17	15
•	Changed x-axis scale from "10 ms/div" to "10 µs/div" in Figure 18	15
•	Changed V <sub>OUT</sub> starting value to 0 V in Figure 19	15
•	Updated Equation 2	
•	Updated Equation 3	
•	Changed DRV package designator from "SON" to "WSON" in Measuring Points for $T_T$ and $T_B$	19

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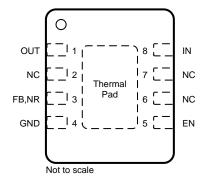
# **Revision History (continued)**

Cr	anges from Revision K (August, 2013) to Revision L	Page
•	Added ESD Ratings table, Feature Description section, Device Functional Modes, Application and Implementation section, Power Supply Recommendations section, Layout section, Device and Documentation Support section, and Mechanical, Packaging, and Orderable Information sections	
•	Added first bullet item in Features list	1
•	Changed fourth bullet item in Features list to "fixed outputs of 1.2 V"	1
•	Changed eighth bullet item in Features list	1
•	Changed last bullet in <i>Features</i> list	
•	Changed last Applications list item	
•	Changed <i>Pin Configuration and Functions</i> section; updated table format and pin descriptions to meet new standards	s 4
•	Changed C <sub>NR</sub> value notation from 0.01 µF to 10 nF throughout <i>Electrical Characteristics</i>	
•	Changed feedback voltage parameter values and measured test conditions	
•	Changed output current limit maximum specified value	
•	Changed power-supply rejection ratio typical specified values for 100 Hz, 10 kHz, and 100 kHz frequency test conditions	
•	Added note (1) to Figure 1	8
•	Changed y-axis title for Figure 6	8
•	Changed y-axis title for Figure 7	8
•	Changed footnote for Figure 13	10
•	Changed reference to noise-reduction capacitor (C <sub>NR</sub> ) to feed-forward capacitor (C <sub>FF</sub> ) in Transient Response	11
•	Changed noise-reduction capacitor to feed-forward capacitor in Figure 16	13
•	Changed references to "noise-reduction capacitor" (C <sub>NR</sub> ) to "feed-forward capacitor" (C <sub>FF</sub> ) and section title from "Feedback Capacitor Requirements" to "Feed-forward Capacitor Requirements" in <i>Feed-Forward Capacitor Requirements</i> section	14
•	Changed C <sub>NR</sub> value notation from 0.01 µF to 10 nF in <i>Output Noise</i> section	
Cr	nanges from Revision J (May, 2011) to Revision K	Page
•	Added last sentence to first paragraph of Startup and Noise Reduction Capacitor section	11
Cŀ	nanges from Revision I (April, 2011) to Revision J	Page
•	Replaced the Dissipation Ratings with Thermal Information	6
•	Revised conditions for <i>Typical Characteristics</i> to include statement about TPS73525 device availability	8
•	Added Estimating Junction Temperature section	18
<u>•</u>	Updated Power Dissipation section	19
Cr	nanges from Revision H (November, 2009) to Revision I	Page
•	Corrected typo in <i>Electrical Characteristics</i> table for $V_{OUT}$ specification, DRV package test conditions, $V_{OUT} \le 2.2V$	7
Ch	nanges from Revision G (March 2009) to Revision H	Page
•	Revised bullet point in <i>Features</i> list to show very low dropout of 280 mV	1
•	Changed dropout voltage typical specification from 250mV to 280mV	
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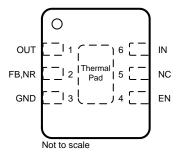


# 5 Pin Configuration and Functions

# DRB Package 8-Pin SON With Exposed Thermal Pad Top View



# DRV Package 6-Pin WSON With Exposed Thermal Pad Top View



NC - No internal connection

# **Pin Functions**

	PIN			
NAME	NO		I/O	DESCRIPTION
NAME	DRV	DRB		
IN	6	8	I	Input supply. A 0.1- $\mu$ F to 1- $\mu$ F, low ESR capacitor must be placed from this pin to ground near the device.
GND	3	4	_	Ground. The pad must be tied to GND.
EN	4	5	1	Driving the enable pin (EN) high turns on the regulator. Driving this pin low puts the regulator into shutdown mode. The EN pin can be connected to the IN pin if not used.
NR	2	3	_	This pin is only available for the fixed voltage versions. Connecting an external capacitor to this pin bypasses noise that is generated by the internal band gap and allows the output noise to be reduced to very low levels. The maximum recommended capacitor is 0.01 $\mu$ F.
FB	2	3	I	This pin is only available for the adjustable version. The FB pin is the input to the control-loop error amplifier, and is used to set the output voltage of the device. This pin must not be left floating.
OUT	1	1	0	This pin is the output of the regulator. A small, $2.2 \cdot \mu F$ ceramic capacitor is required from this pin to ground to assure stability. The minimum output capacitance required for stability is 2 $\mu F$ .
NC	5	2, 6, 7		Not internally connected.
Thermal	pad		_	



# 6 Specifications

# 6.1 Absolute Maximum Ratings

at  $-40^{\circ}$ C  $\leq T_{\perp}$  and  $T_{\Delta} \leq +125^{\circ}$ C (unless otherwise noted). All voltages are with respect to GND. (1)

		MIN	MAX	UNIT
V <sub>IN</sub>		-0.3	7	V
V <sub>EN</sub>	Voltage	-0.3	V <sub>IN</sub> + 0.3	V
V <sub>FB</sub>	Voltage	-0.3	1.6	V
V <sub>OUT</sub>		-0.3	V <sub>IN</sub> + 0.3	V
I <sub>OUT</sub>	Current	Interna	ally limited	Α
P <sub>D(tot)</sub>	Continuous total power dissipation	See Thern	nal Information	
TJ	Operating junction temperature	-40	150	°C
T <sub>stg</sub>	Storage temperature	-55	150	°C

<sup>(1)</sup> Stresses beyond those listed as *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated as *Recommended Operating Conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

# 6.2 ESD Ratings

			VALUE	UNIT
		Human body model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins <sup>(1)</sup>	±2000	V
$V_{(ESD)}$	Electrostatic discharge	Charged device model (CDM), per JEDEC specification JESD22-C101, all pins (2)	±500	V

<sup>(1)</sup> JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

# 6.3 Recommended Operating Conditions

over operating junction temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
$V_{IN}$	Input voltage	2.7		6.5	V
V <sub>OUT</sub>	Output voltage	$V_{FB}$		6	V
I <sub>OUT</sub>	Output current <sup>(1)</sup>	0		500	mA
T <sub>A</sub>	Operating free-air temperature	-40		125	°C
C <sub>IN</sub>	Input capacitor		1		μF
C <sub>OUT</sub>	Output capacitor		2		μF
C <sub>NR</sub>	Noise reduction capacitor		10		nF
C <sub>FF</sub>	Feed-forward capacitor (2)	3	22	1000	pF
R <sub>2</sub>	Feedback resistor (2)	·	110		kΩ

<sup>(1)</sup> When operating at  $T_J$  near 125°C,  $I_{OUT(min)}$  is 500  $\mu A$ .

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<sup>(2)</sup> JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

<sup>(2)</sup> Adjustable version only.



#### 6.4 Thermal Information

			TPS735 <sup>(2)</sup>			
	THERMAL METRIC <sup>(1)</sup>	DRB (SON)	DRV (WSON)	UNIT		
		8 PINS	6 PINS			
$R_{\theta JA}$	Junction-to-ambient thermal resistance (3)	52.2	65.1	°C/W		
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance (4)	59.4	85.6	°C/W		
$R_{\theta JB}$	Junction-to-board thermal resistance	19.3	34.7	°C/W		
ΨЈТ	Junction-to-top characterization parameter (5)	2	1.6	°C/W		
ΨЈВ	Junction-to-board characterization parameter (6)	19.3	35.1	°C/W		
R <sub>0</sub> JC(bot)	Junction-to-case (bottom) thermal resistance (7)	11.8	5.8	°C/W		

- For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.
- (2) Thermal data for the DRB, DCQ, and DRV packages are derived by thermal simulations based on JEDEC-standard methodology as specified in the JESD51 series. The following assumptions are used in the simulations:
  - (a) i. DRB: The exposed pad is connected to the PCB ground layer through a 2 x 2 thermal via array. ii. DRV: The exposed pad is connected to the PCB ground layer through a 2 x 2 thermal via array. Due to size limitation of thermal pad, 0.8-mm pitch array is used which is off the JEDEC standard.
  - (b) i. DRB: The top and bottom copper layers are assumed to have a 20% thermal conductivity of copper representing a 20% copper coverage.
    - ii DRV: The top and bottom copper layers are assumed to have a 20% thermal conductivity of copper representing a 20% copper coverage.
  - (c) These data were generated with only a single device at the center of a JEDEC high-K (2s2p) board with 3-in x 3-in copper area. To understand the effects of the copper area on thermal performance, see the *Power Dissipation* and *Estimating Junction Temperature* sections
- (3) The junction-to-ambient thermal resistance under natural convection is obtained in a simulation on a JEDEC-standard, high-K board, as specified in JESD51-7, in an environment described in JESD51-2a.
- (4) The junction-to-case (top) thermal resistance is obtained by simulating a cold plate test on the top of the package. No specific JEDEC-standard test exists, but a close description can be found in the ANSI SEMI standard G30-88.
- (5) The junction-to-top characterization parameter,  $\psi_{JT}$ , estimates the junction temperature of a device in a real system and is extracted from the simulation data to obtain  $\theta_{JA}$  using a procedure described in JESD51-2a (sections 6 and 7).
- (6) The junction-to-board characterization parameter, ψ<sub>JB</sub>, estimates the junction temperature of a device in a real system and is extracted from the simulation data to obtain θ<sub>JA</sub> using a procedure described in JESD51-2a (sections 6 and 7).
- (7) The junction-to-case (bottom) thermal resistance is obtained by simulating a cold plate test on the exposed (power) pad. No specific JEDEC standard test exists, but a close description can be found in the ANSI SEMI standard G30-88.



# 6.5 Electrical Characteristics

over operating temperature range (–40°C  $\leq$  T $_{J}$   $\leq$  125°C),  $V_{IN}$  =  $V_{OUT(nom)}$  + 0.5 V or 2.7 V (whichever is greater),  $I_{OUT}$  = 1 mA,  $V_{EN}$  =  $V_{IN}$ ,  $C_{OUT}$  = 2.2  $\mu$ F, and  $C_{NR}$  = 10 nF (unless otherwise noted). For the adjustable version (TPS73501),  $V_{OUT}$  = 3 V. Typical values are at  $T_A = 25$ °C.

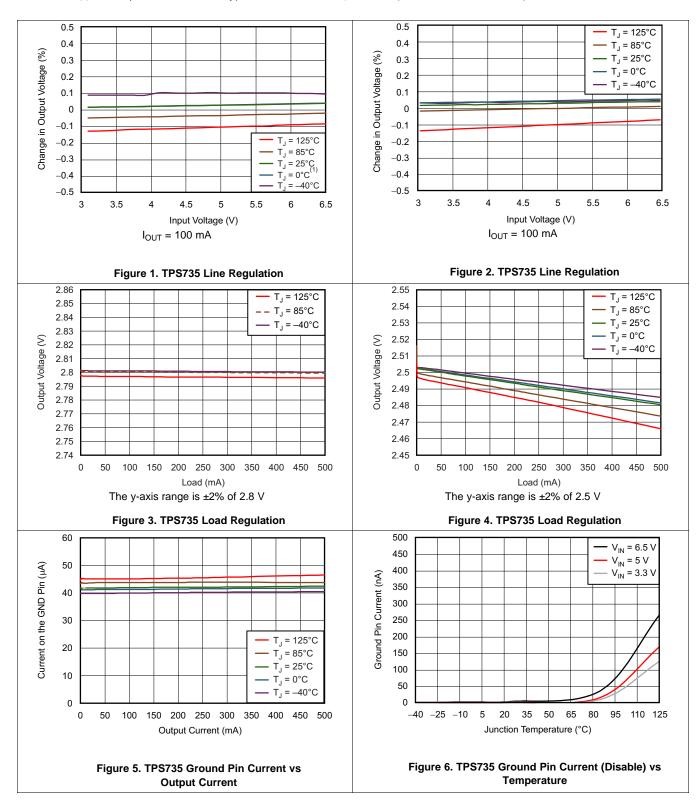
	PARAMETER	TEST COM	IDITIONS	MIN	TYP	MAX	UNIT	
V <sub>IN</sub>	Input voltage <sup>(1)</sup>			2.7		6.5	V	
$V_{FB}$	Internal reference (adjustable version only)	T <sub>J</sub> = 25°C	$T_J = 25^{\circ}C$		1.208	1.220	V	
V <sub>OUT</sub>	Output voltage range (adjustable version only)			V <sub>FB</sub>		6	V	
	DC output accuracy <sup>(1)</sup>	1 mA ≤ I <sub>OUT</sub> ≤ 500 mA,	V <sub>OUT</sub> > 2.2 V	-2%	±1%	2%		
		$V_{OUT} + 0.5 \text{ V} \le V_{IN} < 6.5 \text{ V}$	V <sub>OUT</sub> ≤ 2.2 V	-3%	±1%	3%		
$\Delta V_{OUT(\Delta VIN)}$	Line regulation <sup>(1)</sup>	$V_{OUT(nom)} + 0.5 V \le V_{IN} \le 6.5$	V		0.02		%/V	
$\Delta V_{OUT(\Delta IOUT)}$	Load regulation	$500 \ \mu A \le I_{OUT} \le 500 \ mA$			0.005		%/mA	
V <sub>DO</sub>	Dropout voltage (2) (V <sub>IN</sub> = V <sub>OUT(nom)</sub> - 0.1 V)	I <sub>OUT</sub> = 500 mA			280	500	mV	
I <sub>LIM</sub>	Output current limit	$V_{OUT} = 0.9 \times V_{OUT(nom)}, V_{IN} = V_{IN} \ge 2.7 \text{ V}$	= V <sub>OUT(nom)</sub> + 0.9 V	800	1170	1900	mA	
I <sub>GND</sub>	Ground pin current	10 mA ≤ I <sub>OUT</sub> ≤ 500 mA			45	65	μА	
I <sub>SHDN</sub>	Shutdown current	V <sub>EN</sub> ≤ 0 V	V <sub>EN</sub> ≤ 0 V		0.15	1	μА	
I <sub>FB</sub>	Feedback pin current (adjustable version only)	V <sub>OUT(nom)</sub> = 1.2 V		-0.5		0.5	μΑ	
		V <sub>IN</sub> = 3.85 V V <sub>OUT</sub> = 2.85 V	f = 100 Hz		66			
DODD			f = 1k Hz		68		ID.	
PSRR	Power-supply rejection ratio	$C_{NR} = 0.01  \mu F$	f = 10 kHz		44		dB	
		I <sub>OUT</sub> = 100 mA	f = 100 kHz		22			
.,	0.1.1.1.11	BW = 10 Hz to 100 kHz,	C <sub>NR</sub> = 10 nF	1	1 x V <sub>OUT</sub>		.,	
$V_n$	Output noise voltage	V <sub>OUT</sub> = 2.8 V	C <sub>NR</sub> = none	9	5 × V <sub>OUT</sub>		$\mu V_{RMS}$	
		C <sub>NR</sub> = none	-		45			
	0	C <sub>NR</sub> = 1 nF			45			
t <sub>STR</sub>	Start-up time	C <sub>NR</sub> = 10 nF			50		μS	
		C <sub>NR</sub> = 47 nF			50			
V <sub>EN(HI)</sub>	Enable high (enabled)			1.2			V	
V <sub>EN(LO)</sub>	Enable low (shutdown)					0.4	V	
I <sub>EN(HI)</sub>	Enable pin current, enabled	$V_{EN} = V_{IN} = 6.5 \text{ V}$			0.03	1	μА	
		Shutdown, temperature incre	easing		165			
$T_{sd}$	Thermal shutdown temperature	Reset, temperature decreas	ing		145		°C	
UVLO	Undervoltage lockout	V <sub>IN</sub> rising		1.9	2.2	2.65	V	
V <sub>hys</sub>	Hysteresis	V <sub>IN</sub> falling			70		mV	
,-	=							

<sup>(1)</sup> Minimum  $V_{IN} = V_{OUT} + V_{DO}$  or 2.7 V, whichever is greater. (2)  $V_{DO}$  is not measured for this family of devices with  $V_{OUT(nom)} < 2.8$  V because the minimum  $V_{IN} = 2.7$  V.



# 6.6 Typical Characteristics

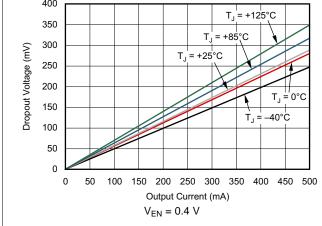
over operating temperature range ( $T_J$ =  $-40^{\circ}C$  to +125 $^{\circ}C$ ),  $V_{IN}$  =  $V_{OUT(nom)}$  + 0.5 V or 2.7 V, whichever is greater;  $I_{OUT}$  = 1 mA,  $V_{EN}$  =  $V_{IN}$ ,  $C_{OUT}$  = 2.2  $\mu$ F,  $C_{NR}$  = 10 nF. Typical values are at  $T_J$  = 25 $^{\circ}C$ , (unless otherwise noted).





# **Typical Characteristics (continued)**

over operating temperature range (T<sub>J</sub>=  $-40^{\circ}$ C to  $+125^{\circ}$ C), V<sub>IN</sub> = V<sub>OUT(nom)</sub> + 0.5 V or 2.7 V, whichever is greater; I<sub>OUT</sub> = 1 mA, V<sub>EN</sub> = V<sub>IN</sub>,C<sub>OUT</sub> = 2.2  $\mu$ F, C<sub>NR</sub> = 10 nF. Typical values are at T<sub>J</sub> = 25 $^{\circ}$ C, (unless otherwise noted).



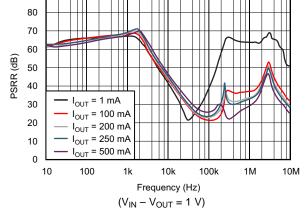
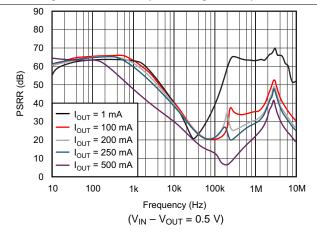


Figure 7. TPS735 Dropout Voltage vs Output Current

Figure 8. Power-Supply Ripple Rejection vs Frequency



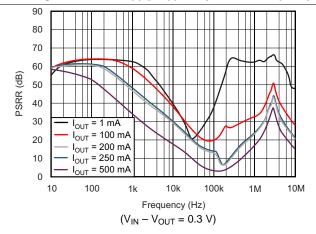
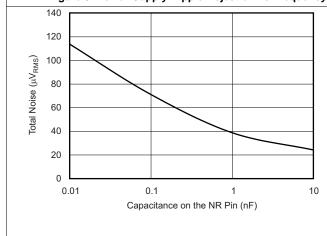


Figure 9. Power-Supply Ripple Rejection vs Frequency

Figure 10. Power-Supply Ripple Rejection vs Frequency



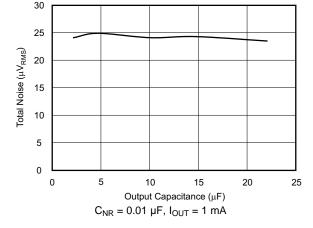


Figure 11. TPS73525 RMS Noise vs  $\mathbf{C}_{\mathrm{NR}}$ 

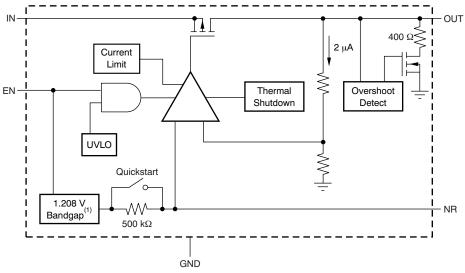
Figure 12. TPS735 RMS Noise vs Cout

# 7 Detailed Description

#### 7.1 Overview

The TPS735 of low dropout (LDO) regulator combines the high performance required by radio frequency (RF) and precision analog applications with ultra-low current consumption. High PSRR is provided by a high-gain, high-bandwidth error loop with good supply rejection and very low headroom ( $V_{IN} - V_{OUT}$ ). Fixed voltage versions provide a noise reduction pin to bypass noise that is generated by the band-gap reference and to improve PSRR. A quick-start circuit fast-charges this capacitor at start-up. The combination of high performance and low ground current make the TPS735 device designed for portable applications. All versions have thermal and overcurrent protection and are specified from  $-40^{\circ}\text{C} \leq T_{.l} \leq +125^{\circ}\text{C}$ .

# 7.2 Functional Block Diagrams



(1) The 1.2-V fixed voltage version has a 1-V band gap instead of a 1.208-V circuit.

Figure 13. Fixed Voltage Versions

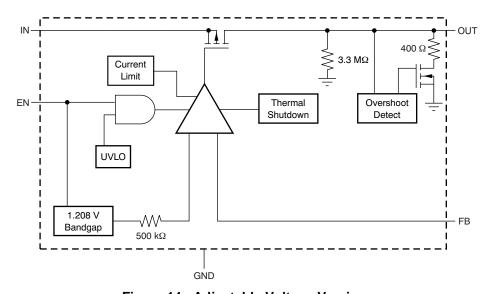


Figure 14. Adjustable Voltage Versions



# 7.3 Feature Description

#### 7.3.1 Internal Current Limit

The TPS735 internal current limit protects the regulator during fault conditions. During current limit, the output sources a fixed amount of current that is independent of the output voltage. For reliable operation, do not operate the device in current limit for extended periods of time.

The PMOS pass element in the TPS735 device contains a built-in body diode that conducts current when the voltage at the OUT pin exceeds the voltage at the IN pin. This current is not limited, so if extended reverse voltage operation is expected, external limiting is appropriate.

#### 7.3.2 Shutdown

The enable pin (EN) is active high and is compatible with standard and low-voltage TTL-CMOS levels. When shutdown capability is not required, the EN pin can connect to the IN pin.

#### 7.3.3 Dropout Voltage

The TPS735 device uses a PMOS pass transistor to achieve low dropout. When  $(V_{IN} - V_{OUT})$  is less than the dropout voltage  $(V_{DO})$ , the PMOS pass device is in the linear region of operation and the input-to-output resistance  $(R_{(IN/OUT)})$  of the PMOS pass element.  $V_{DO}$  scales with the output current because the PMOS device operates like a resistor in dropout.

As with any linear regulator, PSRR and transient response degrades as  $(V_{IN} - V_{OUT})$  approaches dropout. *Typical Characteristics* shows this effect; (see Figure 8 through Figure 10).

# 7.3.4 Start-Up and Noise Reduction Capacitor

Fixed voltage versions of the TPS735 use a quick-start circuit to charge the noise reduction (NR) capacitor ( $C_{NR}$ ) if present (see *Functional Block Diagrams*). This architecture allows the combination of low output noise and fast start-up times. The NR pin is high impedance so a low-leakage  $C_{NR}$  capacitor must be used. Most ceramic capacitors are appropriate in this configuration. A high-quality, COG-type (NPO) dielectric ceramic capacitor is recommended for  $C_{NR}$  when used in environments where abrupt changes in temperature can occur.

For the fastest start-up, first apply  $V_{IN}$ , then drive the enable (EN) pin high. If EN is tied to IN, start-up is slower. See *Typical Applications*. The quick-start switch closes for approximately 135  $\mu$ s. To ensure that  $C_{NR}$  is charged during the quick-start time, use a capacitor with a value of no more than 0.01  $\mu$ F.

#### 7.3.5 Transient Response

As with any regulator, increasing the size of the output capacitor reduces overshoot and undershoot magnitude but increases the transient response duration. In the adjustable version, adding  $C_{FF}$  between the OUT and FB pins improves stability and transient response performance. The transient response of the TPS735 device is enhanced by an active pulldown that engages when the output overshoots by approximately 5% or more when the device is enabled. The pull-down device operates like a  $400-\Omega$  resistor to ground when enabled.

# 7.3.6 Undervoltage Lockout

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The TPS735 device uses an undervoltage lockout circuit to disable the output until the internal circuitry is operates properly. The UVLO circuit contains a deglitch feature so that the UVLO ignores undershoot transients on the input if the transients are less than  $50 \, \mu s$  in duration.

#### 7.3.7 Minimum Load

The TPS735 device is stable with no output load. To meet the specified accuracy, a minimum load of 500  $\mu$ A is required. If the output is below 500  $\mu$ A and if the junction temperature is approximately 125°C, the output can increase enough to turn on the output pulldown. The output pulldown limits voltage drift to 5% (typically) but ground current can increase by approximately 50  $\mu$ A. In most applications, the junction does not reach high temperatures at light loads because little power is dissipated. As a result, the specified ground current is valid at no load in most applications.

Draduat Folder Links, TDS

# **Feature Description (continued)**

#### 7.3.8 Thermal Protection

Thermal protection disables the output when the junction temperature increases to approximately 165°C, which allows the device to cool. When the junction temperature cools to approximately 145°C, the output circuitry is enabled. Depending on power dissipation, thermal resistance, and ambient temperature, the thermal protection circuit cycles on and off. This cycling limits the dissipation of the regulator and protects the regulator from damage as a result of overheating.

Any tendency to activate the thermal protection circuit indicates excessive power dissipation or an inadequate heat sink. For reliable operation, limit junction temperature to 125°C (maximum). To estimate the thermal margin in a complete design (including heat sink), increase the ambient temperature until the thermal protection is triggered. Use worst-case loads and signal conditions. For reliable operation, trigger thermal protection at least 40°C above the maximum expected ambient condition of a particular application. This configuration produces a worst-case junction temperature of 125°C at the highest expected ambient temperature and worst-case load.

The internal protection circuitry of the TPS735 protects against overload conditions. This protection circuitry is not intended to replace proper heat sinking. Continuously running the TPS735 into thermal shutdown degrades device reliability.

# 7.4 Device Functional Modes

#### 7.4.1 Normal Operation

The device regulates to the nominal output voltage under the following conditions:

- The input voltage previously exceeded the UVLO voltage and did not decrease below the UVLO threshold minus V<sub>hys</sub>.
- The input voltage is greater than the nominal output voltage that is added to the dropout voltage.
- The enable voltage has previously exceeded the enable rising threshold voltage and has not decreased below the enable falling threshold.
- The output current is less than the current limit.
- The device junction temperature is within the specified range.

#### 7.4.2 Dropout Operation

If the input voltage is lower than the nominal output voltage plus the specified dropout voltage, but all other conditions are met for normal operation, the device operates in dropout mode. In this condition, the output voltage is equal to the input voltage minus the dropout voltage. The transient performance of the device degrades because the pass device is in a triode state and the LDO operates like a resistor. Line or load transients in dropout can result in large output voltage deviations.

#### 7.4.3 Disabled

The device is disabled under the following conditions:

- The input voltage is less than the UVLO threshold minus V<sub>hys</sub>, or has not yet exceeded the UVLO threshold.
- The enable voltage is less than the enable falling threshold voltage or has not yet exceeded the enable rising threshold.
- The device junction temperature is greater than the thermal shutdown temperature.

Table 1 lists the conditions that result in different modes of operation.

**Table 1. Device Functional Mode Comparison** 

OPERATING MODE	PARAMETER					
OPERATING MODE	V <sub>IN</sub>	V <sub>EN</sub>	I <sub>OUT</sub>	$T_J$		
Normal mode	$V_{IN} > V_{OUTnom} + V_{DO}$ and $V_{IN} > UVLO$	$V_{EN} > V_{EN(HI)}$	I <sub>OUT</sub> < I <sub>LIM</sub>	T <sub>J</sub> < 125°C		
Dropout mode	$UVLO < V_{IN} < V_{OUTnom} + V_{DO}$	$V_{EN} > V_{EN(HI)}$	_	T <sub>J</sub> < 165°C		
Disabled mode (any true condition disables the device)	V <sub>IN</sub> < UVLO - V <sub>hys</sub>	V <sub>EN</sub> < V <sub>EN(LO)</sub>	_	T <sub>J</sub> > 165°C		

Product Folder Links: TPS735



# 8 Application and Implementation

#### **NOTE**

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

# 8.1 Application Information

The TPS735 LDO regulator provides a design with an ultra-low noise, high PSRR, low-dropout linear regulation with a very small ground current (5 µA, typical).

The devices are stable with ceramic capacitors and have a dropout voltage of 280 mV at the full output rating of 500 mA. The features of the TPS735 device enables the LDO regulators to be used in a wide variety of applications with minimal design complexity.

# 8.2 Typical Applications

Figure 15 shows the basic circuit connections for fixed-voltage models. Figure 16 shows the connections for the adjustable output version. R<sub>1</sub> and R<sub>2</sub> can be calculated for any output voltage using the formula in Figure 16.

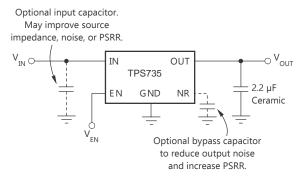


Figure 15. Typical Application Circuit for Fixed-Voltage Versions

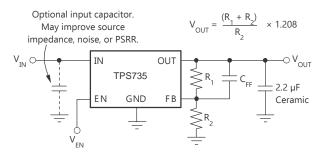


Figure 16. Typical Application Circuit for Adjustable-Voltage Versions



# **Typical Applications (continued)**

#### 8.2.1 Design Requirements

# 8.2.1.1 Input and Output Capacitor Requirements

Although an input capacitor is not required for stability, connecting a 0.1- $\mu$ F to 1- $\mu$ F low-equivalent series-resistance (ESR) capacitor across the input supply near the regulator is good analog design practice. This capacitor counteracts reactive input sources and improves transient response and ripple rejection. A higher-value capacitor may be required if large, fast, rise-time load transients are expected, or if the device is located several inches from the power source. If source impedance is not sufficiently low, a 0.1- $\mu$ F input capacitor may be required to ensure stability.

TheTPS735 device is designed to be stable with standard ceramic output capacitors of values 2  $\mu$ F or larger. X5R- and X7R-type capacitors are best because these capacitors feature minimal variation in value and ESR over temperature. Maximum ESR of the output capacitor is < 1  $\Omega$  and, therefore, the output capacitor type must be ceramic or conductive polymer electrolytic.

#### 8.2.1.2 Feed-Forward Capacitor Requirements

The feed-forward capacitor ( $C_{FF}$ ), shown in Figure 16, is required for stability. For a parallel combination of  $R_1$  and  $R_2$  equal to 250 k $\Omega$ , any value between 3 pF to 1 nF can be used. Fixed-voltage versions have an internal 30-pF feed-forward capacitor that is quick-charged at start-up. Larger value capacitors improve noise slightly. The TPS735 device is stable in unity-gain configurations (the OUT pin is tied to the FB pin) without  $C_{FF}$ .

#### 8.2.2 Detailed Design Procedure

# 8.2.2.1 Output Noise

In most LDO regulators, the band gap is the dominant noise source. If a noise-reduction capacitor ( $C_{NR}$ ) is used with the TPS735 device, the band gap does not contribute significantly to noise. Noise is dominated by the output resistor divider and the error-amplifier input. To minimize noise in a given application, use a 10-nF noise reduction capacitor. For the adjustable version, smaller value resistors in the output resistor divider reduce noise. A parallel combination that produces 2  $\mu$ A of divider current has the same noise performance as a fixed voltage version with a  $C_{NR}$ . To further optimize noise, set the ESR of the output capacitor to approximately 0.2  $\Omega$ . This configuration maximizes phase margin in the control loop, which reduces the total output noise up to 10%. TI recommends a maximum capacitor value of 10 nF.

Equation 1 calculates the approximate integrated output noise from 10 Hz to 100 kHz with a  $C_{NR}$  value of 10 nF.

$$V_{n} (\mu V_{RMS}) = 11(\mu V_{RMS} / V) \times V_{OUT} (V)$$
(1)

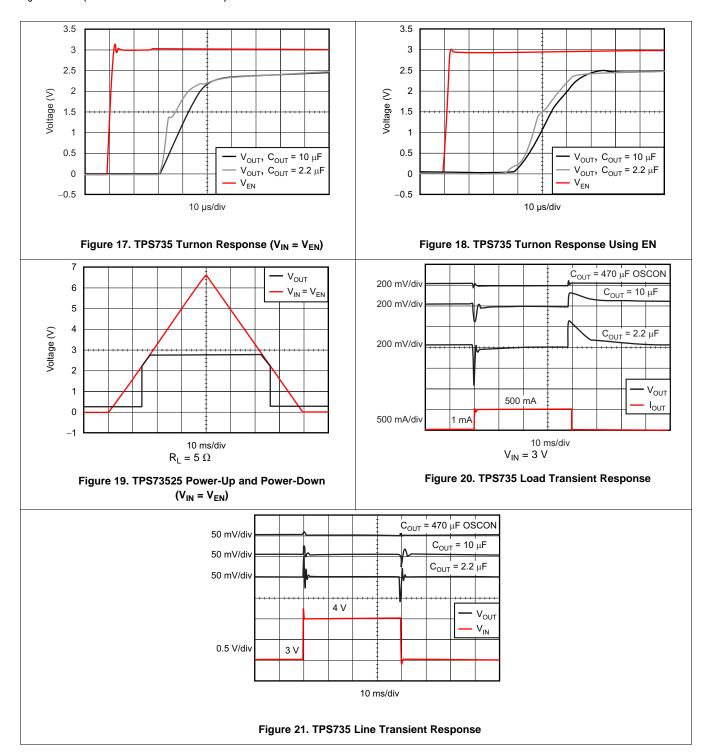
The TPS735adjustable version does not have the noise-reduction pin available, so ultra-low noise operation is not possible. Noise is minimized according to the previously listed recommendations.



# **Typical Applications (continued)**

# 8.2.3 Application Curves

at  $V_{IN} = V_{OUT(nom)} + 0.5$  V or 2.7 V, whichever is greater;  $I_{OUT} = 1$  mA,  $V_{EN} = V_{IN}$ ,  $C_{OUT} = 2.2$   $\mu$ F,  $C_{NR} = 10$  nF, and  $T_J = 25$ °C (unless otherwise noted)



# 9 Power Supply Recommendations

The device is designed to operate from an input voltage supply range between 2.7 V and 6.5 V. The input voltage range must provide adequate headroom for the device to have a regulated output. This input supply must be well-regulated. If the input supply is noisy, additional input capacitors with low ESR can help improve output noise.

# 10 Layout

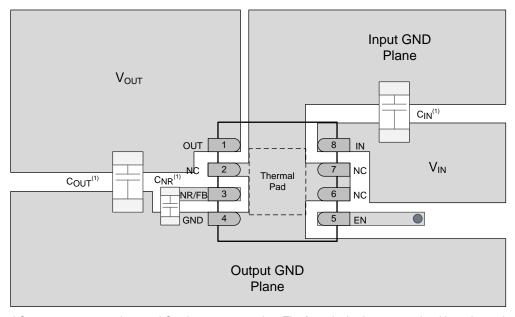
# 10.1 Layout Guidelines

For best overall performance, place all circuit components on the same side of the circuit board and as near to the respective LDO pin connections as possible. Place ground return connections to the input and output capacitor, and to the LDO ground pin as close to each other as possible, connected by a wide, component-side, copper surface. The use of vias and long traces to create LDO component connections is strongly discouraged and negatively affects system performance. This grounding and layout scheme minimizes inductive parasitics, and as a result, reduces load-current transients, minimizes noise, and increases circuit stability. TI recommends using a ground reference plane, and is embedded in the printed circuit board (PCB) itself or located on the bottom side of the PCB opposite the components. This reference plane ensures accuracy of the output voltage, shields the LDO from noise, and operates similar to a thermal plane to spread (or sink) heat from the LDO device when connected to the exposed thermal pad. In most applications, this ground plane is required to meet thermal requirements.

# 10.1.1 Board Layout Recommendations to Improve PSRR and Noise Performance

To improve AC performance (such as PSRR, output noise, and transient response), TI recommends designing the board with separate ground planes for  $V_{IN}$  and  $V_{OUT}$ , with each ground plane connected only at the GND pin of the device. In addition, the ground connection for the bypass capacitor must connect directly to the GND pin of the device.

# 10.2 Layout Example



(1)  $C_{IN}$  and  $C_{OUT}$  are 0603 capacitors and  $C_{NR}$  is a 0402 capacitor. The footprint is shown to scale with package size.

Figure 22. TPS735 Fixed Version Layout Reference Diagram



#### 10.3 Power Dissipation

The ability to remove heat from the die is different for each package type, which presents different considerations in the PCB layout. The PCB area around the device that is free of other components moves the heat from the device to the ambient air. Performance data for JEDEC low- and high-K boards are shown in the *Thermal Information* section. Heavier copper increases the effectiveness in removing heat from the device. The addition of plated through-holes to heat-dissipating layers improves the heat sink effectiveness.

Power dissipation depends on input voltage and load conditions. Power dissipation can be approximated by the product of the output current and the voltage drop across the output pass element, as Equation 2 shows.

$$P_{D} = (V_{IN} - V_{OUT}) \times I_{OUT}$$
(2)

#### NOTE

When the device is used in a condition of high input and low output voltages,  $P_D$  can exceed the junction temperature rating even when the ambient temperature is at room temperature.

Equation 3 is an example calculation for the power dissipation (P<sub>D</sub>) of the DRB package.

$$P_D = (6.5 \text{ V} - 1.2 \text{ V}) \times 500 \text{ mA} = 2.65 \text{ W}$$
 (3)

Power dissipation can be minimized and greater efficiency can be achieved by using the lowest possible input voltage necessary to achieve the required output performance.

On the DRB package, the primary conduction path for heat is through the exposed thermal pad to the PCB. The pad can be connected to ground or left floating. The pad must be attached to an appropriate amount of copper PCB area to ensure that the device does not overheat. The maximum allowable junction-to-ambient thermal resistance depends on the maximum ambient temperature, maximum device junction temperature, and power dissipation of the device. Equation 4 calculates the maximum junction-to-ambient thermal resistance.

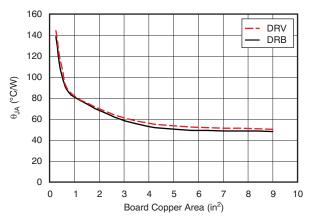
$$R_{\theta JA} = \frac{\left(125^{\circ}C - T_{A}\right)}{P_{D}} \tag{4}$$

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# TEXAS INSTRUMENTS

# **Power Dissipation (continued)**

Figure 23 estimates the maximum  $R_{\theta JA}$  and the minimum amount of PCB copper area required to heat sink.



Note:  $\theta_{JA}$  value at board size of 9 in<sup>2</sup> (that is, 3 in x 3 in) is a JEDEC standard.

Figure 23.  $\theta_{JA}$  vs Board Size

Figure 23 shows the variation of  $\theta_{JA}$  as a function of ground plane copper area in the board. It is intended only as a guideline to demonstrate the effects of heat spreading in the ground plane and must not be used to estimate actual thermal performance in real application environments.

#### NOTE

When the device is mounted on an application PCB, it is strongly recommended to use  $\Psi_{JT}$  and  $\Psi_{JB}$ , as explained in the *Estimating Junction Temperature* section.

# 10.4 Estimating Junction Temperature

Using the thermal metrics  $\Psi_{JT}$  and  $\Psi_{JB}$ , as the table shows, the junction temperature can be estimated with corresponding formulas (Equation 5), which are more accurate than the value of  $T_J$  through calculation with  $\theta_{JA}$ .

$$\begin{split} \Psi_{JT} \colon & T_J = T_T + \Psi_{JT} \bullet P_D \\ \Psi_{JB} \colon & T_J = T_B + \Psi_{JB} \bullet P_D \end{split}$$

where:

- P<sub>D</sub> is the power dissipation calculated with Equation 2,
- T<sub>T</sub> is the temperature at the center-top of the device package, and
- T<sub>B</sub> is the PCB temperature measured 1 mm away from the device package on the PCB surface (as shown in Figure 25).

#### NOTE

Both  $T_T$  and  $T_B$  can be measured on actual application boards using a thermo-gun (an infrared thermometer).

For more information about measuring  $T_T$  and  $T_B$ , see *Using New Thermal Metrics*, available for download at www.ti.com.



# **Estimating Junction Temperature (continued)**

According to Figure 24, the new thermal metrics ( $\Psi_{JT}$  and  $\Psi_{JB}$ ) do not depend on the copper area. Using  $\Psi_{JT}$  or  $\Psi_{JB}$  with Equation 5 can estimate  $T_J$  by measuring  $T_T$  or  $T_B$  on an application board.

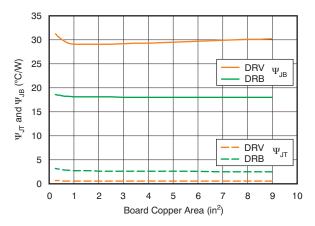
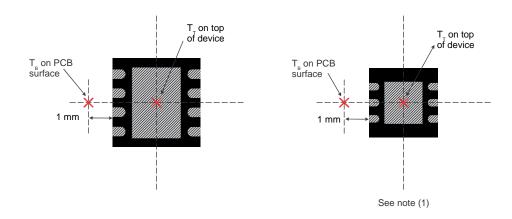


Figure 24.  $\Psi_{\text{JT}}$  and  $\Psi_{\text{JB}}$  vs Board Size



- (a) Example DRB (SON) Package Measurement
- (b) Example DRV (WSON) Package Measurement
- (1) Power dissipation may limit operating range. See *Thermal Information*.

Figure 25. Measuring Points for T<sub>T</sub> and T<sub>B</sub>

# 10.5 Package Mounting

Solder pad footprint recommendations for the TPS735 device is available from the TI website at www.ti.com.

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# 11 Device and Documentation Support

# 11.1 Device Support

#### 11.1.1 Development Support

#### 11.1.1.1 Evaluation Modules

Two evaluation modules (EVMs) are available to assist in the initial circuit performance evaluation using the TPS735. The TPS73501EVM-276 evaluation module and the TPS73525EVM-276 Evaluation Module (and related user guide) can be requested at the TI website through the product folders or purchased directly from the TI eStore.

#### 11.1.2 Device Nomenclature

Table 2. Device Nomenclature (1)

PRODUCT	V <sub>OUT</sub>
TPS735 <b>xx(x)</b> <i>yyyz</i>	<ul> <li>xx(x) is the nominal output voltage. For output voltages with a resolution of 100 mV, two digits are used in the ordering number; otherwise, three digits are used (for example, 33 = 3.3 V; 125 = 1.25 V).</li> <li>yyy is the package designator.</li> <li>z is the tape and reel quantity (R = 3000, T = 250).</li> <li>01 is the adjustable version.</li> </ul>

<sup>(1)</sup> For the most current package and ordering information see the Package Option Addendum at the end of this document, or see the TI web site at www.ti.com.

# 11.2 Documentation Support

#### 11.2.1 Related Documentation

For related documentation, see the following:

• Texas Instruments, TPS735EVM-276 User Guide

#### 11.3 Trademarks

All trademarks are the property of their respective owners.

#### 11.4 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

# 11.5 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

# 12 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.





4-Jul-2020

# **PACKAGING INFORMATION**

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
TPS73501DRBR	ACTIVE	SON	DRB	8	3000	Green (RoHS & no Sb/Br)	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	СВК	Samples
TPS73501DRBT	ACTIVE	SON	DRB	8	250	Green (RoHS & no Sb/Br)	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	СВК	Samples
TPS73501DRVR	ACTIVE	WSON	DRV	6	3000	Green (RoHS & no Sb/Br)	NIPDAU   NIPDAUAG	Level-1-260C-UNLIM	-40 to 125	SDR	Samples
TPS73501DRVT	ACTIVE	WSON	DRV	6	250	Green (RoHS & no Sb/Br)	NIPDAU   NIPDAUAG	Level-1-260C-UNLIM	-40 to 125	SDR	Samples
TPS73512DRBR	ACTIVE	SON	DRB	8	3000	Green (RoHS & no Sb/Br)	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	QTT	Samples
TPS73512DRBT	ACTIVE	SON	DRB	8	250	Green (RoHS & no Sb/Br)	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	QTT	Samples
TPS73515DRBR	ACTIVE	SON	DRB	8	3000	Green (RoHS & no Sb/Br)	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	QWH	Samples
TPS73515DRBT	ACTIVE	SON	DRB	8	250	Green (RoHS & no Sb/Br)	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	QWH	Samples
TPS73525DRBR	ACTIVE	SON	DRB	8	3000	Green (RoHS & no Sb/Br)	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	СВМ	Samples
TPS73525DRBRG4	ACTIVE	SON	DRB	8	3000	Green (RoHS & no Sb/Br)	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	СВМ	Samples
TPS73525DRBT	ACTIVE	SON	DRB	8	250	Green (RoHS & no Sb/Br)	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	СВМ	Samples
TPS73525DRVR	ACTIVE	WSON	DRV	6	3000	Green (RoHS & no Sb/Br)	NIPDAUAG	Level-1-260C-UNLIM	-40 to 125	NSW	Samples
TPS73525DRVT	ACTIVE	WSON	DRV	6	250	Green (RoHS & no Sb/Br)	NIPDAUAG	Level-1-260C-UNLIM	-40 to 125	NSW	Samples
TPS73527DRVR	ACTIVE	WSON	DRV	6	3000	Green (RoHS & no Sb/Br)	NIPDAU	Level-1-260C-UNLIM	-40 to 125	RAK	Samples
TPS73527DRVT	ACTIVE	WSON	DRV	6	250	Green (RoHS & no Sb/Br)	NIPDAU	Level-1-260C-UNLIM	-40 to 125	RAK	Samples
TPS735285DRVR	ACTIVE	WSON	DRV	6	3000	Green (RoHS & no Sb/Br)	NIPDAUAG	Level-1-260C-UNLIM	-40 to 125	RAW	Samples



# PACKAGE OPTION ADDENDUM

4-Jul-2020

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
TPS735285DRVT	ACTIVE	WSON	DRV	6	250	Green (RoHS & no Sb/Br)	NIPDAUAG	Level-1-260C-UNLIM	-40 to 125	RAW	Samples
TPS73533DRBR	ACTIVE	SON	DRB	8	3000	Green (RoHS & no Sb/Br)	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	CVY	Samples
TPS73533DRBT	ACTIVE	SON	DRB	8	250	Green (RoHS & no Sb/Br)	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	CVY	Samples
TPS73533DRVR	ACTIVE	WSON	DRV	6	3000	Green (RoHS & no Sb/Br)	NIPDAU   NIPDAUAG	Level-1-260C-UNLIM	-40 to 125	CVY	Samples
TPS73533DRVT	ACTIVE	WSON	DRV	6	250	Green (RoHS & no Sb/Br)	NIPDAU   NIPDAUAG	Level-1-260C-UNLIM	-40 to 125	CVY	Samples
TPS73534DRBR	ACTIVE	SON	DRB	8	3000	Green (RoHS & no Sb/Br)	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	QTU	Samples
TPS73534DRBT	ACTIVE	SON	DRB	8	250	Green (RoHS & no Sb/Br)	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	QTU	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

**Green:** TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.



# PACKAGE OPTION ADDENDUM

4-Jul-2020

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

#### OTHER QUALIFIED VERSIONS OF TPS735:

Automotive: TPS735-Q1

NOTE: Qualified Version Definitions:

Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects

PACKAGE MATERIALS INFORMATION

www.ti.com 16-Oct-2020

# TAPE AND REEL INFORMATION



# TAPE DIMENSIONS KO P1 BO W Cavity AO

	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

# QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



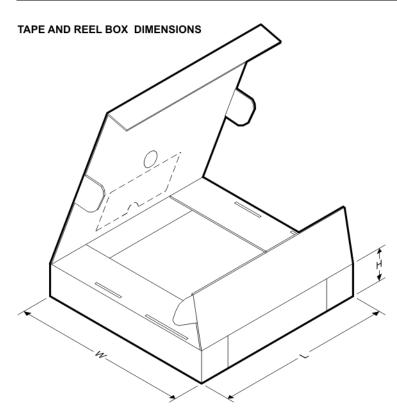
\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadran
TPS73501DRBR	SON	DRB	8	3000	330.0	12.4	3.3	3.3	1.1	8.0	12.0	Q2
TPS73501DRBT	SON	DRB	8	250	180.0	12.5	3.3	3.3	1.1	8.0	12.0	Q2
TPS73501DRVR	WSON	DRV	6	3000	178.0	8.4	2.25	2.25	1.0	4.0	8.0	Q2
TPS73501DRVT	WSON	DRV	6	250	179.0	8.4	2.2	2.2	1.2	4.0	8.0	Q2
TPS73501DRVT	WSON	DRV	6	250	178.0	8.4	2.25	2.25	1.0	4.0	8.0	Q2
TPS73512DRBR	SON	DRB	8	3000	330.0	12.4	3.3	3.3	1.1	8.0	12.0	Q2
TPS73512DRBT	SON	DRB	8	250	180.0	12.4	3.3	3.3	1.1	8.0	12.0	Q2
TPS73515DRBR	SON	DRB	8	3000	330.0	12.4	3.3	3.3	1.1	8.0	12.0	Q2
TPS73515DRBT	SON	DRB	8	250	180.0	12.5	3.3	3.3	1.1	8.0	12.0	Q2
TPS73525DRBR	SON	DRB	8	3000	330.0	12.4	3.3	3.3	1.1	8.0	12.0	Q2
TPS73525DRBT	SON	DRB	8	250	180.0	12.5	3.3	3.3	1.1	8.0	12.0	Q2
TPS73525DRVR	WSON	DRV	6	3000	179.0	8.4	2.2	2.2	1.2	4.0	8.0	Q2
TPS73525DRVT	WSON	DRV	6	250	179.0	8.4	2.2	2.2	1.2	4.0	8.0	Q2
TPS73527DRVR	WSON	DRV	6	3000	179.0	8.4	2.2	2.2	1.2	4.0	8.0	Q2
TPS73527DRVR	WSON	DRV	6	3000	178.0	8.4	2.25	2.25	1.0	4.0	8.0	Q2
TPS73527DRVT	WSON	DRV	6	250	179.0	8.4	2.2	2.2	1.2	4.0	8.0	Q2
TPS735285DRVR	WSON	DRV	6	3000	179.0	8.4	2.2	2.2	1.2	4.0	8.0	Q2
TPS735285DRVT	WSON	DRV	6	250	179.0	8.4	2.2	2.2	1.2	4.0	8.0	Q2

# **PACKAGE MATERIALS INFORMATION**

www.ti.com 16-Oct-2020

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPS73533DRBR	SON	DRB	8	3000	330.0	12.4	3.3	3.3	1.1	8.0	12.0	Q2
TPS73533DRBR	SON	DRB	8	3000	330.0	12.4	3.3	3.3	1.1	8.0	12.0	Q2
TPS73533DRBT	SON	DRB	8	250	180.0	12.5	3.3	3.3	1.1	8.0	12.0	Q2
TPS73533DRVR	WSON	DRV	6	3000	179.0	8.4	2.2	2.2	1.2	4.0	8.0	Q2
TPS73533DRVR	WSON	DRV	6	3000	178.0	8.4	2.25	2.25	1.0	4.0	8.0	Q2
TPS73533DRVT	WSON	DRV	6	250	179.0	8.4	2.2	2.2	1.2	4.0	8.0	Q2
TPS73533DRVT	WSON	DRV	6	250	178.0	8.4	2.25	2.25	1.0	4.0	8.0	Q2
TPS73534DRBR	SON	DRB	8	3000	330.0	12.4	3.3	3.3	1.1	8.0	12.0	Q2
TPS73534DRBT	SON	DRB	8	250	180.0	12.4	3.3	3.3	1.1	8.0	12.0	Q2



\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TPS73501DRBR	SON	DRB	8	3000	338.0	355.0	50.0
TPS73501DRBT	SON	DRB	8	250	338.0	355.0	50.0
TPS73501DRVR	WSON	DRV	6	3000	205.0	200.0	33.0
TPS73501DRVT	WSON	DRV	6	250	203.0	203.0	35.0
TPS73501DRVT	WSON	DRV	6	250	205.0	200.0	33.0
TPS73512DRBR	SON	DRB	8	3000	853.0	449.0	35.0
TPS73512DRBT	SON	DRB	8	250	210.0	185.0	35.0
TPS73515DRBR	SON	DRB	8	3000	338.0	355.0	50.0



# **PACKAGE MATERIALS INFORMATION**

www.ti.com 16-Oct-2020

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TPS73515DRBT	SON	DRB	8	250	338.0	355.0	50.0
TPS73525DRBR	SON	DRB	8	3000	338.0	355.0	50.0
TPS73525DRBT	SON	DRB	8	250	338.0	355.0	50.0
TPS73525DRVR	WSON	DRV	6	3000	203.0	203.0	35.0
TPS73525DRVT	WSON	DRV	6	250	203.0	203.0	35.0
TPS73527DRVR	WSON	DRV	6	3000	203.0	203.0	35.0
TPS73527DRVR	WSON	DRV	6	3000	205.0	200.0	33.0
TPS73527DRVT	WSON	DRV	6	250	203.0	203.0	35.0
TPS735285DRVR	WSON	DRV	6	3000	203.0	203.0	35.0
TPS735285DRVT	WSON	DRV	6	250	203.0	203.0	35.0
TPS73533DRBR	SON	DRB	8	3000	338.0	355.0	50.0
TPS73533DRBR	SON	DRB	8	3000	853.0	449.0	35.0
TPS73533DRBT	SON	DRB	8	250	338.0	355.0	50.0
TPS73533DRVR	WSON	DRV	6	3000	203.0	203.0	35.0
TPS73533DRVR	WSON	DRV	6	3000	205.0	200.0	33.0
TPS73533DRVT	WSON	DRV	6	250	203.0	203.0	35.0
TPS73533DRVT	WSON	DRV	6	250	205.0	200.0	33.0
TPS73534DRBR	SON	DRB	8	3000	853.0	449.0	35.0
TPS73534DRBT	SON	DRB	8	250	210.0	185.0	35.0



Images above are just a representation of the package family, actual package may vary. Refer to the product data sheet for package details.

4206925/F







# NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

  2. This drawing is subject to change without notice.

  3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.





NOTES: (continued)

- 4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature
- number SLUA271 (www.ti.com/lit/slua271).

  5. Vias are optional depending on application, refer to device data sheet. If some or all are implemented, recommended via locations are shown.





NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.







# NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

  2. This drawing is subject to change without notice.

  3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.





NOTES: (continued)

- 4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
- 5. Vias are optional depending on application, refer to device data sheet. If some or all are implemented, recommended via locations are shown.





NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.





Images above are just a representation of the package family, actual package may vary. Refer to the product data sheet for package details.

4203482/L







#### NOTES:

- All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.





NOTES: (continued)

- 4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
- 5. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.





NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



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